(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
20 November 2008 (20.11.2008)

PCT

(10) International Publication Number
WO 2008/138881 A1

(51) International Patent Classification:
H01L 21/02 (2006.01)

(21) International Application Number:
PCT/EP2008/055737

(22) International Filing Date: 9 May 2008 (09.05.2008)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
07108145.9 14 May 2007 (14.05.2007) EP

(71) Applicant *(for all designated States except US)*: **BASF SE** [DE/DE]; 67056 Ludwigshafen (DE).

(72) Inventors; and
(75) Inventors/Applicants *(for US only)*: **FERSTL, Berthold** [DE/DE]; Hardweg 6, 64625 Bensheim (DE). **KÜHNER, Andreas** [DE/DE]; Blütenallee 27, 64291 Darmstadt (DE).

(74) Common Representative: **BASF SE**; 67056 Ludwigshafen (DE).

(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MT, NL, NO, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:
— *with international search report*

WO 2008/138881 A1

(54) Title: METHOD FOR REMOVING ETCHING RESIDUES FROM SEMICONDUCTOR COMPONENTS

(57) Abstract: A method for cleaning structured surfaces of semiconductor components to remove photoresist and etching residues after the etching of the surface, comprising: a) removal of the photoresist, b) treatment of the surface with an acidic aqueous solution comprising one or more acids and one or more oxidizing agents, c) treatment of the surface with an alkaline aqueous solution and d) washing of the surface with demineralized water, the steps a), b) and c) being effected before step d).